

EFC4K105NUZ

Power MOSFET for 1-2 Cells Lithium-ion Battery Protection

22 V, 3.55 mΩ, 25 A, Dual N-Channel

This Power MOSFET features a low on-state resistance. This device is suitable for applications such as power switches of portable machines. Best suited for 1-2 cells lithium-ion battery applications.

Features

- 2.5 V Drive
- Common-Drain Type
- ESD Diode-Protected Gate
- This device is Pb-Free, Halogen Free and RoHS Compliance

Applications

- 1-2 Cells Lithium-ion Battery Charging and Discharging Switch

Specifications

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Source to Source Voltage	V_{SSS}	22	V
Gate to Source Voltage	V_{GSS}	± 12	V
Source Current (DC)	I_S	25	A
Source Current (Pulse) $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$	I_{SP}	100	A
Total Dissipation (Note 1)	P_T	2.5	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 1)	$R_{\theta JA}$	50	$^\circ\text{C/W}$

1. Surface mounted on ceramic substrate ($5000 \text{ mm}^2 \times 0.8 \text{ mm}$).

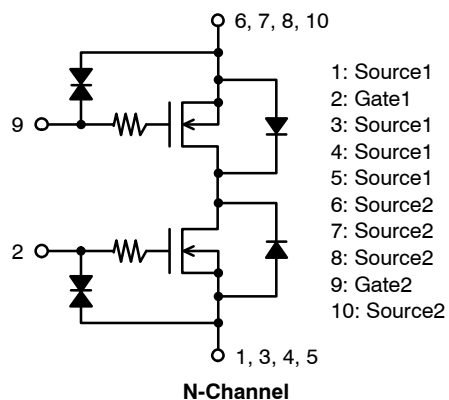


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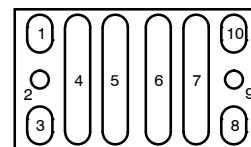
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V_{SSS}	$R_{SS(ON)} \text{ MAX}$	$I_S \text{ MAX}$
22 V	3.55 mΩ @ 4.5 V	25 A
	3.65 mΩ @ 3.8 V	
	5.3 mΩ @ 3.1 V	
	7.2 mΩ @ 2.5 V	

ELECTRICAL CONNECTION



PIN ASSIGNMENT



MARKING DIAGRAM



NZ = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

EFC4K105NUZ

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)SSS}$	Source to Source Breakdown Voltage	$I_S = 1\text{ mA}$, $V_{GS} = 0\text{ V}$	22			V
I_{SSS}	Zero-Gate Voltage Source Current	$V_{SS} = 17.6\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 8\text{ V}$, $V_{SS} = 0\text{ V}$			± 1	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{SS} = 10\text{ V}$, $I_S = 1\text{ mA}$	0.4		1.3	V
$R_{SS(on)}$	Static Source to Source On-State Resistance	$I_S = 5\text{ A}$, $V_{GS} = 4.5\text{ V}$	1.8	2.7	3.55	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 3.8\text{ V}$	1.9	2.8	3.65	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 3.1\text{ V}$	2.0	3.3	5.3	$\text{m}\Omega$
		$I_S = 5\text{ A}$, $V_{GS} = 2.5\text{ V}$	2.2	4.0	7.2	$\text{m}\Omega$
$t_d(on)$	Turn-ON Delay Time	$V_{SS} = 10\text{ V}$, $V_{GS} = 3.8\text{ V}$, $I_S = 5\text{ A}$ $R_g = 10\text{ k}\Omega$ Switching Test Circuit		13		μs
t_r	Rise Time			35		μs
$t_d(off)$	Turn-OFF Delay Time			185		μs
t_f	Fall Time			78		μs
Qg	Total Gate Charge	$V_{SS} = 10\text{ V}$, $V_{GS} = 3.8\text{ V}$, $I_S = 5\text{ A}$		43		nC
$V_{F(S-S)}$	Forward Source to Source Voltage	$I_S = 3\text{ A}$, $V_{GS} = 0\text{ V}$		0.75	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

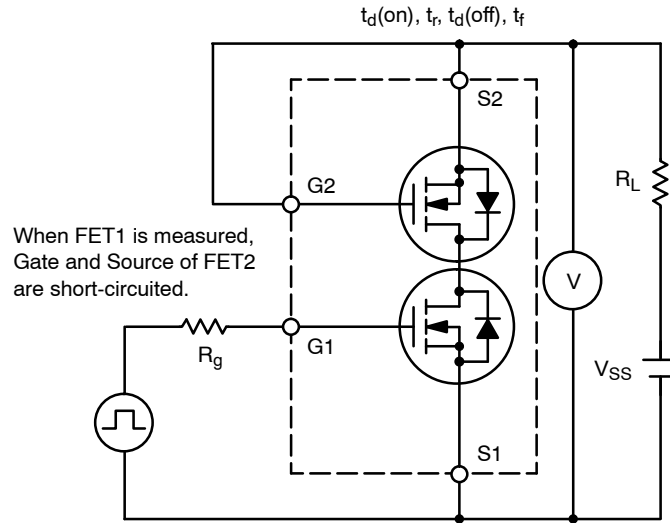


Figure 1. Switching Test Circuit

ORDERING INFORMATION

Device	Marking	Package	Shipping [†] (Qty / Packing)
EFC4K105NUZTDG	NZ	WLCSOP10, 3.40 x 1.96 x 0.10 (Pb-Free / Halogen Free)	5,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, [BRD8011/D](#).

TYPICAL CHARACTERISTICS

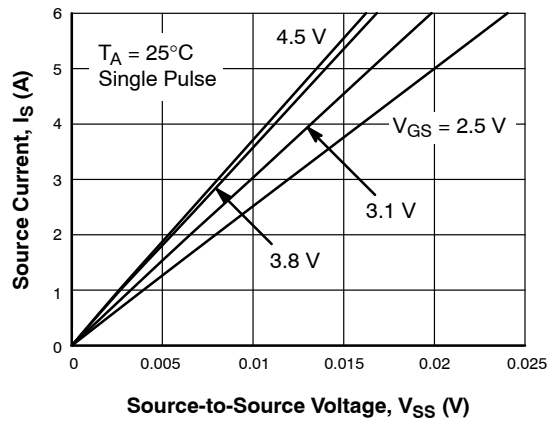


Figure 2. On-Region Characteristics

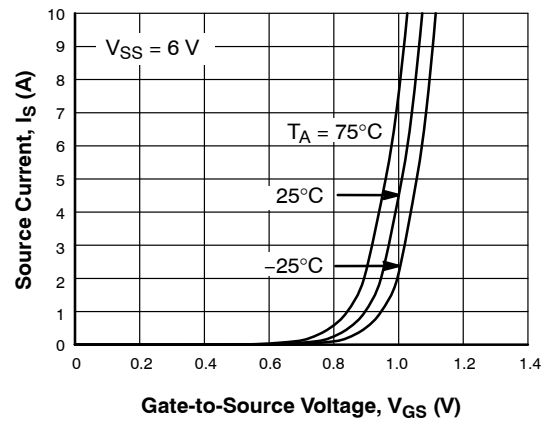


Figure 3. Transfer Characteristics

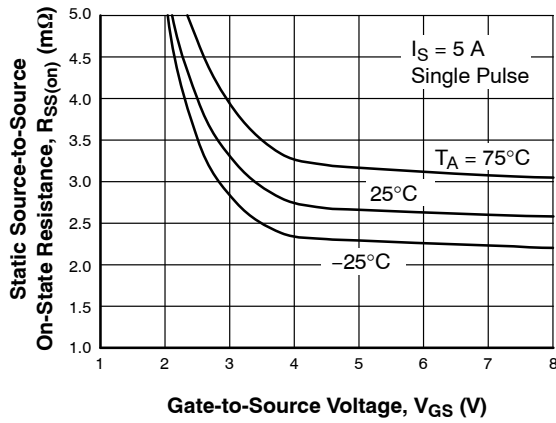


Figure 4. On-Resistance vs. Gate-to-Source Voltage

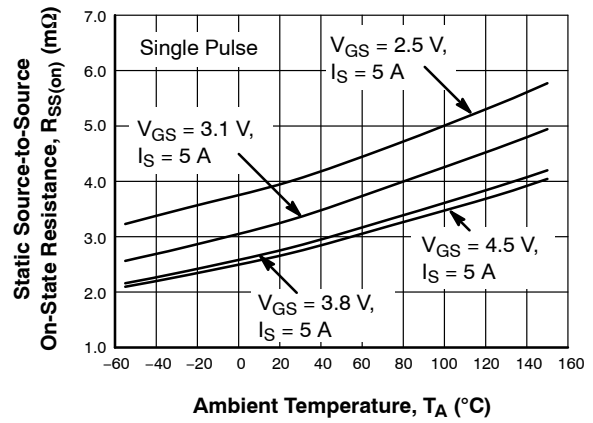


Figure 5. On-Resistance vs. Temperature

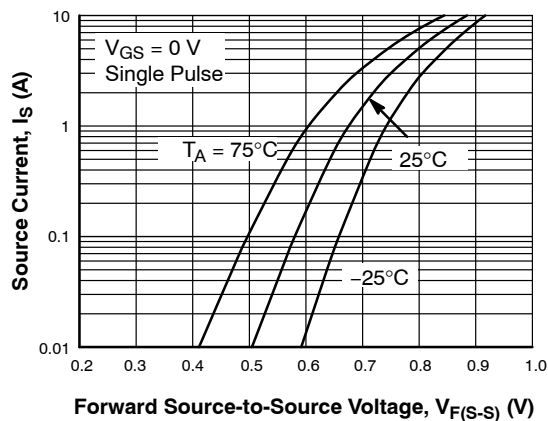


Figure 6. Forward Source-to-Source Voltage vs. Current

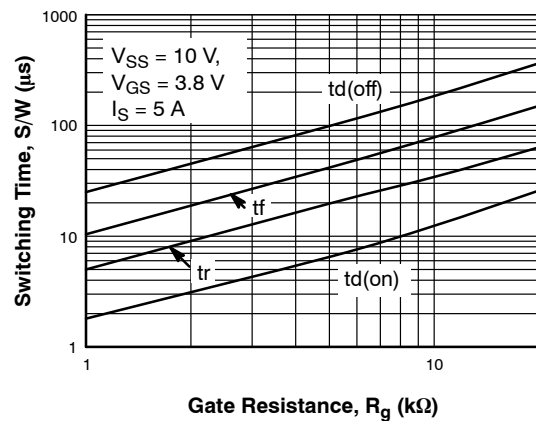


Figure 7. Switching Time vs. Gate Resistance

TYPICAL CHARACTERISTICS

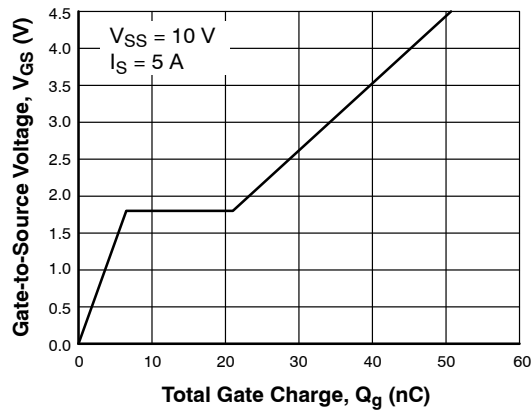


Figure 8. Gate-to-Source Voltage vs. Total Charge

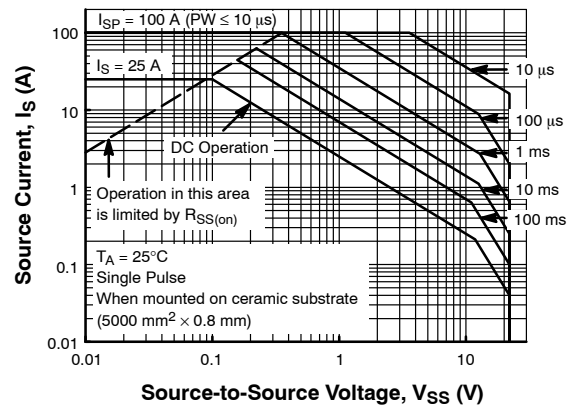


Figure 9. Safe Operating Area

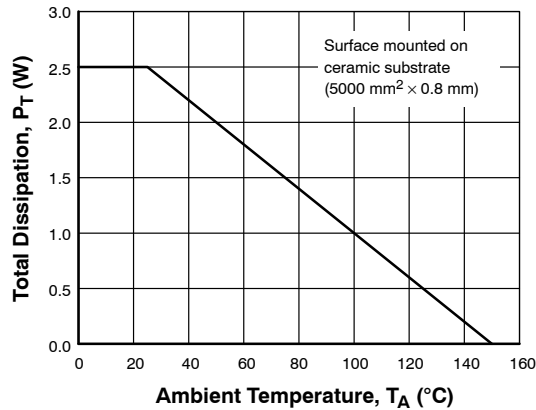


Figure 10. Total Dissipation vs. Temperature

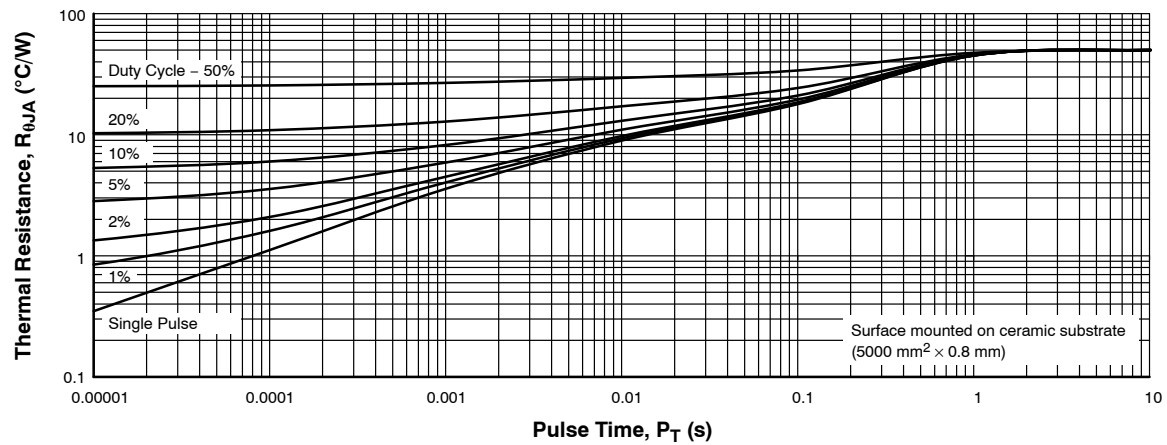


Figure 11. Thermal Response

Note on Usage: Since the EFC4K105NUZ is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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